12-22-06

PATENT 1/21

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE
(MBHB Case No. 05-720-US3)

In re Application of:	)	
	)	
Kouvetakis, et al.	)	Examiner: To Be Assigned
	)	
Serial No.: 10/559,980	)	Group Art Unit: 2812
	)	
Filed: December 8, 2005	)	Confirmation No. 6555
	)	
For: **Method for preparing ge1-x-ysnxey (e=p, as, sb) semiconductors and related si-ge-sn-e and si-ge-e analogs**	)	

TRANSMITTAL LETTER

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

In regard to the above identified application:

1. We are transmitting herewith the attached:

   - ☒ Transmittal Letter (1 sheet)
   - ☒ Information Disclosure Statement (IDS) (11 sheets);
   - ☒ IDS Form 1449 (13 sheets);
   - ☒ 123 Cited References (Copies of references 13-123 are enclosed herewith);
   - ☒ Return Receipt Postcard.

Return Receipt Postcard.

2. With respect to fees:

   ☒ No fee is required

3. Please charge any additional fees or credit overpayment to Deposit Account No. **13-2490**.

4. CERTIFICATE OF MAILING BY "EXPRESS MAIL" UNDER 37 CFR § 1.10: The undersigned hereby certifies that this Transmittal Letter and the papers, as described hereinabove, are being deposited with the United States Postal Service with sufficient postage as "Express Mail Post Office to Addressee" in a box addressed to: PO Box 1450, Alexandria, VA 22313-1450, on this **20th** day of **December, 2006**. Express Mail No. **EV840507818US**.

Respectfully submitted,

By: _____
David S. Harper
Reg. No. 42,636

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE
(Case No. 05-720-US3)

In the Application of:			
	Kouvetakis et al.	Art Unit:	2812
Serial No.:	10/559,980		
		Examiner:	To be assigned
Filed:	December 8, 2005		
		Confirmation No.	6555
For:	Method for Preparing gel-x-ysnxey (e=p, as, sb) Semiconductors and related si-ge-sn-e and si-ge-e analogs		

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Pursuant to 37 C.F.R. Section 1.97 - 1.99, the Applicant wishes to make the following references of record in the above-identified application. This Information Disclosure Statement is in compliance with the continuing duty of candor as set forth in 37 C.F.R. Section 1.56. Copies of the references cited below are enclosed. These references are also listed on the enclosed PTO Form 1449.

In the judgment of the undersigned, portions of the listed references may be material to the Examiner's consideration of the presently pending claims. However, the references have not been reviewed in sufficient detail to make any other representation and, in particular, no representation is intended as to the relative relevance between references, whether cited in this or prior statements. This statement is not a representation that the listed references have effective dates early enough to be "prior art" within the meaning of 35 U.S.C. Section 102 or Section 103.

This Information Disclosure Statement is being filed:

☒ within three months of the filing date of a national application; within three months of the date of entry into the national stage as set forth in 37 C.F.R. § 1.491 in an international application; or before the mailing date of a first Office Action on the merits. 37 C.F.R. §1.97 (b)

☐ **after** three months of the filing date of a national application, or the date of entry into the national stage as set forth in 37 C.F.R. § 1.491 in an international application; or **after** the mailing date of a first Office Action on the merits, but **before** the mailing date of a Final Action under 37 C.F.R. § 1.113 or a Notice of Allowance under 37 C.F.R. § 1.311 (whichever occurs first), and includes (37 C.F.R. § 1.97 (c):

☐ the Certification under 37 C.F.R. § 1.97(e) (see "Certification" below)

OR

☐ the fee of $180.00 set forth in 37 C.F.R. § 1.17(p) (see "Fees" below).

☐ **after** a Final Action under 37 C.F.R. § 1.113 or a Notice of Allowance under 37 C.F.R. § 1.311 (whichever occurs first), but before, or simultaneously with, the payment of the issue fee, and includes the Certification under 37 C.F.R. § 1.97(e) (see "Certification" below), and the Petition Fee set forth in 37 C.F.R. § 1.17(i) (see "Fees" and "Method of Payment of Fees" below). Applicants hereby petitions for consideration of the Information Disclosure Statement submitted herewith and the accompanying references in examination of the subject patent application.

CERTIFICATION

☐ The **undersigned** hereby certifies that each item of information contained in the Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign patent application not more than three months prior to the filing of the Information Disclosure Statement.

☐ The **undersigned** hereby certifies that no item of information contained in the Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign patent application or, to the knowledge of the person signing the certification after making reasonable inquiry, was known to any individual designated in 37 C.F.R. § 1.56(c) more than three months prior to the filing of the Information Disclosure Statement.

FEES

☒ **No fee** is owed by the applicant(s).

☐ The **IDS Fee of $180.00** under 37 C.F.R. § 1.17(p) is enclosed herewith.

METHOD OF PAYMENT OF FEES

☐ Attached is a check in the amount of $180.00

CERTIFICATE OF MAILING VIA EXPRESS MAIL DELIVERY under 37 C.F.R. § 1.10. I hereby certify that the attached paper of fee is being deposited with the United States Postal Service "Express Mail Post Office to Addressee" Service under 37 C.F.R.§ 1.10 on the date indicated above and is addressed to Commissioner for Patents, Box 1450, Alexandria, VA, 22313-1450, on this **20th** day of **December, 2006.** **Express Mail No. EV840507818US.**

Respectfully submitted,

David S. Harper
Registration No. 42,636

United States Patents

1. Murthy, et al., U.S. Publication No. US 2003-0157787 A1, Published on August 21, 2003.
2. Kouvetakis, et al., U.S. Publication No. US 2006-0134895 A1, Published on June 22, 2006.
3. Kouvetakis, et al., U.S. Publication No. US 2006-0236923 A1, Published on October 26, 2006.
4. Kouvetakis, et al., U.S. Publication No. US 2006-0163612-A1, Published on July 27, 2006.
5. Kouvetakis, et al., U.S. Patent No. 6,911,084, Issued on June 28, 2005.
6. Sugawara, et al., U.S. Patent No. 5,532,183, Issued on July 2, 1996.
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8. Oguro, U.S. Patent No.: 5,714,415, Issued on February 3, 1998.
9. Mani, U.S. Patent No.: 6,410,434, Issued on June 25, 2002.
10. Cordone, et al., U.S. Patent No.: 6,723,621 B1, Issued on April 20, 2004.
11. Soref, et al., U.S. Patent No.: 6,897,471, Issued on May 24, 2005.
12. Doppalapudi, et al., U.S. Patent No.: 6,441,716, Issued on August 27, 2002.

Foreign Documents

13. PCT Patent Publication No. WO 2005/001902, published January 6, 2005.

14. PCT Patent Publication No. WO 2004/114368, published December 29, 2004.

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Commonly owned Co-Pending Applications:

1. Kouvetakis, et al., U.S. Patent Application No. 10/559,981, Filed on December 8, 2005.

2. Kouvetakis, et al., U.S. Patent Application No. 10/559,979, Filed on December 8, 2005.

In accordance with MPEP Sections 609 and 707.05(b), it is requested the document cited (including any cited in applicant's specification which is not repeated on the attached Form PTO-1449) be given thorough consideration and that it be cited of record in the prosecution history of the present application by initialing on Form PTO-1449. Such initialing is requested even if the Examiner does not consider a cited document to be sufficiently pertinent to use in a rejection, or otherwise does not consider it to be prior art for any reason, or even if the Examiner does not believe that the guidelines for citation have been fully complied with. This is requested so that each document becomes listed on the face of the patent issuing on the present application.

Respectfully submitted,

Date: 12/20/06 By: _____

David S. Harper
Reg. No. 42,636
McDonnell, Boehnen Hulbert & Berghoff LLP
300 South Wacker Drive, Suite #3100
Chicago, IL 60606

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		Applicant: Kouvetakis, et al.	
		Filing Date: December 8, 2005	Group: 2812

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use several sheets if necessary)

U.S. PATENT DOCUMENTS

Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
	1.	US 2003-0157787 A1	August 21, 2003	Murthy, et al.			
	2.	US 2006-0134895 A1	June 22, 2006	Kouvetakis, et al.			
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	14.	WO 2004/114368	December 29, 2004	PCT				
	15.	WO 2005/015609	February 17, 2005	PCT				
	16.	WO 2003/033781	April 24, 2003	PCT				
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CHICAGO, ILLINOIS 60606
TELEPHONE (312) 913-0001

FORM PTO-1449 (Rev. 2-32)	U.S. Department of Commerce Patent and Trademark Office	Atty. Docket No.	Serial No.
		05-720-US3	10/559,980
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COMMONLY OWNED CO-PENDING APPLICATIONS

Examiner Initial		
	1.	Kouvetakis, et al., U.S. Patent Application No. 10/559,981, Filed on December 8, 2005.
	2.	Kouvetakis, et al., U.S. Patent Application No. 10/559,979, Filed on December 8, 2005.

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